Vladimir Gavrilenko

List of Publications by Year
in descending order

202	2,240	257101 24	329751 37
papers	citations	h-index	g-index

203	203	203	1210
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Observation of three-dimensional massless Kane fermions in a zinc-blende crystal. Nature Physics, 2014, 10, 233-238.	6.5	190
2	Temperature-driven massless Kane fermions in HgCdTe crystals. Nature Communications, 2016, 7, 12576.	5.8	73
3	Stimulated emission from HgCdTe quantum well heterostructures at wavelengths up to 19.5â€‰Î¼m. Applied Physics Letters, 2017, 111, .	1.5	58
4	Pressure- and temperature-driven phase transitions in HgTe quantum wells. Physical Review B, 2016, 94, .	1.1	57
5	Effective third-order nonlinearities in metallic refractory titanium nitride thin films. Optical Materials Express, 2015, 5, 2395.	1.6	50
6	High-responsivity terahertz detection by on-chip InGaAs/GaAs field-effect-transistor array. Applied Physics Letters, 2011, 98, .	1.5	49
7	HgCdTe-based heterostructures for terahertz photonics. APL Materials, 2017, 5, .	2.2	49
8	Cyclotron resonance in HgTe/CdTe-based heterostructures in high magnetic fields. Nanoscale Research Letters, 2012, 7, 534.	3.1	47
9	Cyclotron resonance and interband optical transitions in HgTe/CdTe(0â€‰1â€‰3) quantum well heterostructures. Semiconductor Science and Technology, 2011, 26, 125011.	1.0	43
10	Experimental study of frequency multipliers based on a GaAs/AlAs semiconductor superlattices in the terahertz frequency range. Semiconductors, 2012, 46, 121-125.	0.2	43
11	Temperature-driven single-valley Dirac fermions in HgTe quantum wells. Physical Review B, 2017, 96, .	1.1	38
12	Efficient long wavelength interband photoluminescence from HgCdTe epitaxial films at wavelengths up to 26â€‰Î¼m. Applied Physics Letters, 2014, 104, .	1.5	35
13	Study of lifetimes and photoconductivity relaxation in heterostructures with Hg x Cd1 â^' x Te/Cd y Hg1 â^' y Te quantum wells. Semiconductors, 2012, 46, 1362-1366.	0.2	34
14	Long wavelength stimulated emission up to 9.5â€‰Î¼m from HgCdTe quantum well heterostructures. Applied Physics Letters, 2016, 108, .	1.5	34
15	Exchange enhancement of the g factor in InAs/AlSb heterostructures. Semiconductors, 2008, 42, 828-833.	0.2	31
16	Spectra and kinetics of THz photoconductivity in narrow-gap Hg_{1â€“x}Cd_xTe (x< 0.2) epitaxial films. Semiconductor Science and Technology, 2013, 28, 125007.	1.0	29
17	Time resolved photoluminescence spectroscopy of narrow gap Hg1â^'xCdxTe/CdyHg1â^'yTe quantum well heterostructures. Applied Physics Letters, 2014, 105, 022102.	1.5	28
18	GaAsSb/GaAs strained structures with quantum wells for lasers with emission wavelength near 1.3 Î¼m. Semiconductors, 2010, 44, 405-412.	0.2	27

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19	Terahertz spectroscopy of quantum-well narrow-bandgap HgTe/CdTe-based heterostructures. JETP Letters, 2010, 92, 756-761.	0.4	27
20	Terahertz photoconductivity of double acceptors in narrow gap HgCdTe epitaxial films grown by molecular beam epitaxy on GaAs(013) and Si(013) substrates. Semiconductor Science and Technology, 2017, 32, 095007.	1.0	27
21	Impurity breakdown and terahertz luminescence in n-GaN epilayers under external electric field. Journal of Applied Physics, 2009, 106, 123523.	1.1	26
22	Anticrossing of Landau levels in HgTe/CdHgTe (013) quantum wells with an inverted band structure. JETP Letters, 2015, 100, 790-794.	0.4	26
23	Stimulated emission in the 28â€“35 Î¼m wavelength range from Peltier cooled HgTe/CdHgTe quantum well heterostructures. Optics Express, 2018, 26, 12755.	1.7	26
24	Electron transport and detection of terahertz radiation in a GaN/AlGaN submicrometer field-effect transistor. Semiconductors, 2007, 41, 232-234.	0.2	24
25	Persistent photoconductivity in InAs/AlSb heterostructures with double quantum wells. Semiconductors, 2010, 44, 616-622.	0.2	24
26	Terahertz radiation generation in multilayer quantum-cascade heterostructures. Technical Physics Letters, 2017, 43, 362-365.	0.2	24
27	Temperature-dependent terahertz spectroscopy of inverted-band three-layer InAs/GaSb/InAs quantum well. Physical Review B, 2018, 97, .	1.1	24
28	Electron transport and terahertz radiation detection in submicrometer-sized GaAs/AlGaAs field-effect transistors with two-dimensional electron gas. Physics of the Solid State, 2004, 46, 146-149.	0.2	23
29	Spin splitting in HgTe/CdHgTe (013) quantum well heterostructures. JETP Letters, 2010, 92, 63-66.	0.4	23
30	Radiative recombination in narrow gap HgTe/CdHgTe quantum well heterostructures for laser applications. Journal of Physics Condensed Matter, 2018, 30, 495301.	0.7	22
31	High performance single emitter homojunction interfacial work function far infrared detectors. Journal of Applied Physics, 2004, 95, 512-519.	1.1	21
32	Temperature-dependent magnetospectroscopy of HgTe quantum wells. Physical Review B, 2016, 94, .	1.1	21
33	Fundamental Limits to Far-Infrared Lasing in Auger-Suppressed HgCdTe Quantum Wells. ACS Photonics, 2020, 7, 98-104.	3.2	21
34	Electron-electron interaction and spin-orbit coupling in InAs/AlSb heterostructures with a two-dimensional electron gas. Semiconductors, 2011, 45, 110-117.	0.2	20
35	Temperature limitations for stimulated emission in 3â€“4 Î¼m range due to threshold and non-threshold Auger recombination in HgTe/CdHgTe quantum wells. Applied Physics Letters, 2020, 117, 083103.	1.5	20
36	Shallow acceptors in strained Ge/Ge1â^'x Six heterostructures with quantum wells. Semiconductors, 2000, 34, 563-567.	0.2	19

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37	High-field splitting of the cyclotron resonance absorption in strained<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi>p</mml:mi><mml:mtext>-InGaAs</mml:mtext><mml:mo>/</mml:mo><mml:mtext>GaAs</mml:mtext></mml:mrow></mml:math> wells. Physical Review B, 2009, 79, .	1.1	19
38	Theory ofg-factor enhancement in narrow-gap quantum well heterostructures. Journal of Physics Condensed Matter, 2011, 23, 385601.	0.7	19
39	Room-temperature intracavity difference-frequency generation in butt-joint diode lasers. Applied Physics Letters, 2008, 92, 021122.	1.5	18
40	Features of the persistent photoconductivity in InAs/AlSb heterostructures with double quantum wells and a tunneling-transparent barrier. Semiconductors, 2012, 46, 1396-1401.	0.2	18
41	Rashba spin splitting and exchange enhancement of the g factor in InAs/AlSb heterostructures with a two-dimensional electron gas. Semiconductors, 2012, 46, 1163-1170.	0.2	18
42	Specific features of the spectra and relaxation kinetics of long-wavelength photoconductivity in narrow-gap HgCdTe epitaxial films and heterostructures with quantum wells. Semiconductors, 2013, 47, 1438-1441.	0.2	18
43	Spectra of Persistent Photoconductivity in InAsâˆ•AlSb Quantum-Well Heterostructures. Semiconductors, 2005, 39, 22.	0.2	17
44	Coherent Emission in the Vicinity of 10 THz due to Auger-Suppressed Recombination of Dirac Fermions in HgCdTe Quantum Wells. ACS Photonics, 2021, 8, 3526-3535.	3.2	17
45	Cyclotron Resonance in Doped and Undoped InAsâˆ•AlSb Heterostructures with Quantum Wells. Semiconductors, 2005, 39, 62.	0.2	16
46	Nonlinear mode mixing in dual-wavelength semiconductor lasers with tunnel junctions. Applied Physics Letters, 2007, 90, 171106.	1.5	16
47	Cyclotron resonance study in InAs/AlSb quantum well heterostructures with two occupied electronic subbands. Journal of Applied Physics, 2012, 111, 093711.	1.1	16
48	Long-wavelength injection lasers based on Pb1â€“x Sn x Se alloys and their use in solid-state spectroscopy. Semiconductors, 2015, 49, 1623-1626.	0.2	16
49	Effect of electron-electron interaction on cyclotron resonance in high-mobility InAs/AlSb quantum wells. Journal of Applied Physics, 2015, 117, 112813.	1.1	16
50	Magneto-transport in inverted HgTe quantum wells. Npj Quantum Materials, 2019, 4, .	1.8	16
51	Type IIâ€“type I conversion of GaAs/GaAsSb heterostructure energy spectrum under optical pumping. Journal of Applied Physics, 2013, 113, 163107.	1.1	15
52	Balance-equation method for simulating terahertz quantum-cascade lasers using a wave-function basis with reduced dipole moments of tunnel-coupled states. Quantum Electronics, 2019, 49, 913-918.	0.3	15
53	Carrier Recombination, Longâ€Wavelength Photoluminescence, and Stimulated Emission in HgCdTe Quantum Well Heterostructures. Physica Status Solidi (B): Basic Research, 2019, 256, 1800546.	0.7	15
54	Terahertz emission and photoconductivity in n-type GaAs/AlGaAs quantum wells: the role of resonant impurity states. Semiconductors, 2010, 44, 1394-1397.	0.2	14

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55	Features of impurity-photoconductivity relaxation in boron-doped silicon. Semiconductors, 2012, 46, 1387-1391.	0.2	14
56	Spin-wave excitations and electron spin resonance in symmetric and asymmetric narrow-gap quantum wells. Physical Review B, 2013, 87, .	1.1	14
57	Terahertz Injection Lasers Based on a PbSnSe Solid Solution with an Emission Wavelength up to 50 Î¼m and Their Application in the Magnetospectroscopy of Semiconductors. Semiconductors, 2018, 52, 1590-1594.	0.2	14
58	Temperature Dependences of the Threshold Current and Output Power of a Quantum-Cascade Laser Emitting at 3.3 THz. Semiconductors, 2018, 52, 1380-1385.	0.2	14
59	Massless Dirac fermions in III-V semiconductor quantum wells. Physical Review B, 2019, 99, .	1.1	14
60	Terahertz detection of magnetic field-driven topological phase transition in HgTe-based transistors. Applied Physics Letters, 2015, 107, .	1.5	13
61	Terahertz imaging of Landau levels in HgTe-based topological insulators. Applied Physics Letters, 2016, 108, .	1.5	13
62	Landau level spectroscopy of valence bands in HgTe quantum wells: effects of symmetry lowering. Journal of Physics Condensed Matter, 2019, 31, 145501.	0.7	13
63	Cyclotron resonance in HgTe/CdTe(013) narrowband heterostructures in quantized magnetic fields. JETP Letters, 2012, 95, 406-410.	0.4	12
64	Wide-aperture detector of terahertz radiation based on GaAs/InGaAs transistor structure with large-area slit grating gate. Technical Physics Letters, 2010, 36, 365-368.	0.2	11
65	Long wavelength superluminescence from narrow gap HgCdTe epilayer at 100â€‰K. Applied Physics Letters, 2015, 107, .	1.5	11
66	Auger recombination in narrow gap HgCdTe/CdHgTe quantum well heterostructures. Journal of Applied Physics, 2021, 129, .	1.1	11
67	Cyclotron resonance quantum Hall effect detector. Semiconductor Science and Technology, 2001, 16, 300-303.	1.0	10
68	Kinetics of terahertz photoconductivity in p-Ge under impurity breakdown conditions. Semiconductors, 2010, 44, 1476-1479.	0.2	10
69	Detection of terahertz radiation by tightly concatenated InGaAs field-effect transistors integrated on a single chip. Applied Physics Letters, 2014, 104, 163508.	1.5	10
70	Features of Photoluminescence of Double Acceptors in HgTe/CdHgTe Heterostructures with Quantum Wells in a Terahertz Range. JETP Letters, 2019, 109, 657-662.	0.4	10
71	Shallow acceptors in Ge/GeSi strained multilayer heterostructures with quantum wells. JETP Letters, 1997, 65, 209-214.	0.4	9
72	Fano resonance study in impurity photocurrent spectra of bulk GaAs and GaAs quantum wells doped with shallow donors. Physical Review B, 2007, 75, .	1.1	9

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73	The effect of exchange interaction on quasiparticle Landau levels in narrow-gap quantum well heterostructures. Journal of Physics Condensed Matter, 2012, 24, 135601.	0.7	9
74	Magnetospectroscopy of double HgTe/CdHgTe quantum wells. Semiconductors, 2016, 50, 1532-1538.	0.2	9
75	Bipolar Persistent Photoconductivity in HgTe/CdHgTe (013) Double Quantum-Well Heterostructures. Semiconductors, 2018, 52, 1586-1589.	0.2	9
76	Plasmon recombination in narrowgap HgTe quantum wells. Journal of Physics Communications, 2020, 4, 115012.	0.5	9
77	Effect of magnetic field quantization on the shallow acceptor spectrum in strained Ge/GeSi heterostructures. Physical Review B, 2002, 66, .	1.1	8
78	Exchange interaction effects in electron spin resonance: Larmor theorem violation in narrow-gap quantum well heterostructures. Journal of Physics Condensed Matter, 2012, 24, 252201.	0.7	8
79	On the band spectrum in p-type HgTe/CdHgTe heterostructures and its transformation under temperature variation. Semiconductors, 2017, 51, 1531-1536.	0.2	8
80	The cyclotron resonance of holes in InGaAs/GaAs heterostructures with quantum wells in quantizing magnetic fields. Semiconductors, 2010, 44, 1492-1494.	0.2	7
81	Rashba spin splitting and cyclotron resonance in strained InGaAs/InP heterostructures with a two-dimensional electron gas. Semiconductors, 2013, 47, 1485-1491.	0.2	7
82	Infrared magneto-spectroscopy of two-dimensional and three-dimensional massless fermions: A comparison. Journal of Applied Physics, 2015, 117, 112803.	1.1	7
83	Long-wavelength stimulated emission and carrier lifetimes in HgCdTe-based waveguide structures with quantum wells. Semiconductors, 2016, 50, 1651-1656.	0.2	7
84	Terahertz injection lasers based on PbSnSe alloy with an emission wavelength up to 46.5 Î¼m. Semiconductors, 2016, 50, 1669-1672.	0.2	7
85	Sub-terahertz FET detector with self-assembled Sn-nanothreads. Journal Physics D: Applied Physics, 2020, 53, 075102.	1.3	7
86	Mid-IR stimulated emission in Hg(Cd)Te/CdHgTe quantum well structures up to 200 K due to suppressed Auger recombination. Laser Physics, 2021, 31, 015801.	0.6	7
87	Toward Peltier-cooled mid-infrared HgCdTe lasers: Analyzing the temperature quenching of stimulated emission at â^¼6â€‰l¼m wavelength from HgCdTe quantum wells. Journal of Applied Physics, 2021, 130, .	1.1	7
88	Current Oscillations under Lateral Transport in GaAsâ•InGaAs Quantum Well Heterostructures. Semiconductors, 2005, 39, 44.	0.2	6
89	Magnetoabsorption in narrow-gap HgCdTe epitaxial layers in the terahertz range. Semiconductors, 2013, 47, 1545-1550.	0.2	6
90	Exchange enhancement of the electron g-factor in a two-dimensional semimetal in HgTe quantum wells. Semiconductors, 2015, 49, 1627-1633.	0.2	6

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91	Investigation of possibility of VLWIR lasing in HgCdTe based heterostructures. Journal of Physics: Conference Series, 2015, 647, 012008.	0.3	6
92	Impurity-induced photoconductivity of narrow-gap Cadmiumâ€“Mercuryâ€“Telluride structures. Semiconductors, 2015, 49, 1605-1610.	0.2	6
93	Detection of Terahertz Radiation by Dense Arrays of InGaAs Transistors. International Journal of High Speed Electronics and Systems, 2015, 24, 1550002.	0.3	6
94	Mercury vacancies as divalent acceptors in Hg y Te1 â€“ y /Cd x Hg1 â€“ x Te structures with quantum wells. Semiconductors, 2016, 50, 1662-1668.	0.2	6
95	Investigation of HgCdTe waveguide structures with quantum wells for long-wavelength stimulated emission. Semiconductors, 2017, 51, 1557-1561.	0.2	6
96	Chain of Dirac spectrum loops of nodes in crossed magnetic and electric fields. Physical Review B, 2018, 97, .	1.1	6
97	Terahertz Photoluminescence of Double Acceptors in Bulky Epitaxial HgCdTe Layers and HgTe/CdHgTe Structures with Quantum Wells. Journal of Experimental and Theoretical Physics, 2018, 127, 1125-1129.	0.2	6
98	Effect of Features of the Band Spectrum on the Characteristics of Stimulated Emission in Narrow-Gap Heterostructures with HgCdTe Quantum Wells. Semiconductors, 2018, 52, 1375-1379.	0.2	6
99	Second-Harmonic Generation of Subterahertz Gyrotron Radiation by Frequency Doubling in InP:Fe and Its Application for Magnetospectroscopy of Semiconductor Structures. Semiconductors, 2019, 53, 1217-1221.	0.2	6
100	Optical Studies and Transmission Electron Microscopy of HgCdTe Quantum Well Heterostructures for Very Long Wavelength Lasers. Nanomaterials, 2021, 11, 1855.	1.9	6
101	Infrared radiation from hot holes during spatial transport in selectively doped InGaAs/GaAs heterostructures with quantum wells. JETP Letters, 1996, 64, 520-524.	0.4	5
102	Resonant states of shallow acceptors in uniaxially deformed germanium. Journal of Experimental and Theoretical Physics, 2001, 93, 1296-1301.	0.2	5
103	Experimental study of nonlinear mode mixing in dual-wavelength semiconductor lasers. Laser Physics, 2007, 17, 684-687.	0.6	5
104	Studying the frequency tuning of pulsed terahertz quantum cascade lasers. Radiophysics and Quantum Electronics, 2012, 54, 609-615.	0.1	5
105	Investigation of magnetoabsorption at different temperatures in HgTe/CdHgTe quantum-well heterostructures in pulsed magnetic fields. Semiconductors, 2015, 49, 1611-1615.	0.2	5
106	Exchange enhancement of the electron g factor in strained InGaAs/InP heterostructures. Semiconductors, 2015, 49, 191-198.	0.2	5
107	Magnetoabsorption of Dirac Fermions in InAs/GaSb/InAs â€œThree-Layerâ€•Gapless Quantum Wells. JETP Letters, 2017, 106, 727-732.	0.4	5
108	Experimental Observation of Temperature-Driven Topological Phase Transition in HgTe/CdHgTe Quantum Wells. Condensed Matter, 2019, 4, 27.	0.8	5

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109	Probing States of a Double Acceptor in CdHgTe Heterostructures via Optical Gating. JETP Letters, 2020, 111, 575-581.	0.4	5
110	Stimulated emission of plasmon-LO mode in narrow gap HgTe/CdHgTe quantum wells. Journal of Optics (United Kingdom), 2021, 23, 115001.	1.0	5
111	Specific Growth Features of Nanostructures for Terahertz Quantum Cascade Lasers and Their Physical Properties. Semiconductors, 2020, 54, 1092-1095.	0.2	5
112	Mid-infrared stimulated emission in HgCdTe/CdHgTe quantum well heterostructures at room temperature. Optical Engineering, 2020, 60, .	0.5	5
113	Far Infrared Emission and Absorption (Amplification) under Real Space Transfer and Population Inversion in Shallow Multi-Quantum-Wells. Physica Status Solidi (B): Basic Research, 1997, 204, 563-565.	0.7	4
114	On the impurity photoconductivity of uniaxially stressed p-Ge. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 680-682.	0.8	4
115	A multifrequency interband two-cascade laser. Semiconductors, 2007, 41, 1209-1213.	0.2	4
116	Difference-frequency generation in a butt-join diode laser. Semiconductors, 2009, 43, 208-211.	0.2	4
117	Cyclotron Resonance of Extremely Conductive 2D Holes in High Ge Content Strained Heterostructures. Journal of Low Temperature Physics, 2010, 159, 216-221.	0.6	4
118	Relaxation of the impurity photoconductivity inp-Ge/Ge_{1â^'x}Si_xquantum well heterostructures. Semiconductor Science and Technology, 2011, 26, 085009.	1.0	4
119	Determination of the heterojunction type in structures with GaAsSb/GaAs quantum wells with various antimony fractions by optical methods. Semiconductors, 2012, 46, 1376-1380.	0.2	4
120	Effect of the direct capture of holes with the emission of optical phonons on impurity-photoconductivity relaxation in p-Si:B. Semiconductors, 2015, 49, 187-190.	0.2	4
121	Polarization-Sensitive Fourier-Transform Spectroscopy of HgTe/CdHgTe Quantum Wells in the Far Infrared Range in a Magnetic Field. JETP Letters, 2018, 108, 329-334.	0.4	4
122	Magnetoconductivity and Terahertz Response of a HgCdTe Epitaxial Layer. Sensors, 2018, 18, 4341.	2.1	4
123	Magnetooptics of HgTe/CdTe Quantum Wells with Giant Rashba Splitting in Magnetic Fields up to 34 T. Semiconductors, 2018, 52, 1386-1391.	0.2	4
124	Calculation of Multiply Charged States of Impurity-Defect Centers in Epitaxial Hg1 â€“xCdxTe Layers. Semiconductors, 2018, 52, 1369-1374.	0.2	4
125	Residual-Photoconductivity Spectra in HgTe/CdHgTe Quantum-Well Heterostructures. Semiconductors, 2019, 53, 1363-1366.	0.2	4
126	Study of the Auger Recombination Energy Threshold in a Series of Waveguide Heterostructures with HgTe/Cd0.7Hg0.3Te QWs Near 14 Î¼m. Semiconductors, 2019, 53, 1154-1157.	0.2	4

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127	Terahertz Spectroscopy of Two-Dimensional Semimetal in Three-Layer InAs/GaSb/InAs Quantum Well. JETP Letters, 2019, 109, 96-101.	0.4	4
128	Calculation of Wave Functions of Resonant Acceptor States in Narrow-Gap CdHgTe Compounds. Semiconductors, 2020, 54, 827-831.	0.2	4
129	Feasibility of lasing in the GaAs Reststrahlen band with HgTe multiple quantum well laser diodes. Journal Physics D: Applied Physics, 2021, 54, 175108.	1.3	4
130	Urbach tail and nonuniformity probe of HgCdTe thin films and quantum well heterostructures grown by molecular beam epitaxy. Optical Engineering, 2020, 60, .	0.5	4
131	Time constant of the far-IR response of a quantum Hall device. Nanotechnology, 2001, 12, 453-456.	1.3	3
132	Fano resonances in the impurity photoexcitation spectra of semiconductors doped with shallow donors. Journal of Experimental and Theoretical Physics, 2005, 101, 708-716.	0.2	3
133	Fano resonance in the impurity photoconductivity spectrum of InP doped with shallow donors. Physics of the Solid State, 2008, 50, 1211-1214.	0.2	3
134	Fano resonances in the impurity photocurrent spectra of GaAs samples and an InGaAs/GaAsP quantum-well heterostructure doped with shallow acceptors. Journal of Experimental and Theoretical Physics, 2009, 109, 466-471.	0.2	3
135	Resonance detection of terahertz radiation in submicrometer field-effect GaAs/AlGaAs transistors with two-dimensional electron gas. Semiconductors, 2009, 43, 528-531.	0.2	3
136	High-resolution emission spectra of pulsed terahertz quantum-cascade lasers. Semiconductors, 2010, 44, 1467-1471.	0.2	3
137	Relaxation kinetics of impurity photoconductivity in p-Si:B with various levels of doping and degrees of compensation in high electric fields. Semiconductors, 2013, 47, 1461-1464.	0.2	3
138	Cyclotron resonance of dirac fermions in InAs/GaSb/InAs quantum wells. Semiconductors, 2017, 51, 38-42.	0.2	3
139	Terahertz Emission from HgCdTe QWs under Long-Wavelength Optical Pumping. Journal of Infrared, Millimeter, and Terahertz Waves, 2020, 41, 750-757.	1.2	3
140	Photothermal Ionization Spectroscopy of Mercury Vacancies in HgCdTe Epitaxial Films. JETP Letters, 2021, 113, 402-408.	0.4	3
141	Terahertz plasmons in doped HgTe quantum well heterostructures: dispersion, losses, and amplification. Applied Optics, 2021, 60, 8991.	0.9	3
142	Shallow-impurity-assisted transitions in the course of submillimeter magnetoabsorption of strained Ge/GeSi(111) quantum-well heterostructures. Physics of the Solid State, 2004, 46, 125-129.	0.2	2
143	Intersubband cyclotron resonance of holes in strained Ge/GeSi(111) heterostructures with germanium wide quantum wells and cyclotron resonance of 1L electrons in GeSi layers. Physics of the Solid State, 2004, 46, 130-137.	0.2	2
144	Frequency shift in a system of two laser diodes. Semiconductors, 2007, 41, 1364-1368.	0.2	2

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145	Emission spectra of terahertz quantum cascade laser. Radiophysics and Quantum Electronics, 2009, 52, 494-499.	0.1	2
146	Diagnostics of quantum cascade structures by optical methods in the near infrared region. Semiconductors, 2012, 46, 1411-1414.	0.2	2
147	Observation of topological phase transition by terahertz photoconductivity in HgTeâ€based transistors. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 534-537.	0.8	2
148	Temperature-driven massless Kane fermions in HgCdTe crystals. , 2016, , .		2
149	Terahertz emission from CdHgTe/HgTe quantum wells with an inverted band structure. Semiconductors, 2016, 50, 915-919.	0.2	2
150	Evolution of the Impurity Photoconductivity in CdHgTe Epitaxial Films with Temperature. Semiconductors, 2019, 53, 1266-1271.	0.2	2
151	Magnetoabsorption in HgCdTe/CdHgTe Quantum Wells in Tilted Magnetic Fields. JETP Letters, 2019, 109, 191-197.	0.4	2
152	Continuous-Wave Stimulated Emission in the 10â€“14-Î¼m Range under Optical Excitation in HgCdTe/CdHgTe-QW Structures with Quasirelativistic Dispersion. Semiconductors, 2020, 54, 1371-1375.	0.2	2
153	Shallow acceptors in strained multiquantum-well Ge/Ge1âˆ’x Six heterostructures. Semiconductors, 1998, 32, 1106-1110.	0.2	1
154	Negative Photoconductivity of Selectively Doped SiGeâˆ•Si : B Heterostructures with a Two-Dimensional Hole Gas in the Middle-Infrared Range. Physics of the Solid State, 2005, 47, 46.	0.2	1
155	First experiments and prospects of intracavity difference -frequency generation of mid/far-infrared and terahertz radiation in diode lasers. , 2008, , .		1
156	Magnetic field dependence of the photoresponse time of GaAs/AlGaAs quantum Hall effect device. Semiconductor Science and Technology, 2008, 23, 095014.	1.0	1
157	Cyclotron resonance in HgCdTe-based heterostructures in strong magnetic fields. Journal of Physics: Conference Series, 2013, 461, 012038.	0.3	1
158	Effects of Rashba spin splitting and exchange interaction in electron spin resonance in narrow-gap quantum well heterostructures. Journal of Physics: Conference Series, 2013, 456, 012021.	0.3	1
159	Detection of Terahertz Radiation by Dense Arrays of InGaAs Transistors. Selected Topics in Electornics and Systems, 2015, , 31-53.	0.2	1
160	Far and Mid IR Stimulated Emission in HgCdTe QW Heterostructures. , 2019, , .		1
161	Investigation of the Photosensitivity of Narrow-Gap and Gapless HgCdTe Solid Solutions in the Terahertz and Sub-Terahertz Range. Semiconductors, 2020, 54, 1096-1102.	0.2	1
162	Photoluminescence Spectra of InAs/GaInSb/InAs Quantum Wells in the Mid-Infrared Region. Semiconductors, 2020, 54, 1119-1122.	0.2	1

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163	Express Characterization of the HgCdTe/CdHgTe Quantum Well Waveguide Heterostructures with the Quasi-Relativistic Carrier Dispersion Law by Room-Temperature Photoluminescence Spectroscopy. Technical Physics Letters, 2021, 47, 154-157.	0.2	1
164	Effective Third-Order Nonlinearities in Refractory Plasmonic TiN Thin Films. , 2016, , .		1
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